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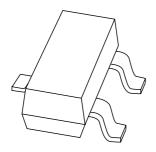
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMBS3904 NPN general purpose transistor

Product data sheet Supersedes data of 1999 Apr 22 2004 Feb 02



NPN general purpose transistor

PMBS3904

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 40 V).

APPLICATIONS

• General purpose switching and amplification, e.g. telephony and professional communication equipment.

DESCRIPTION

NPN transistor in a plastic SOT23 package. PNP complement: PMBS3906.

MARKING

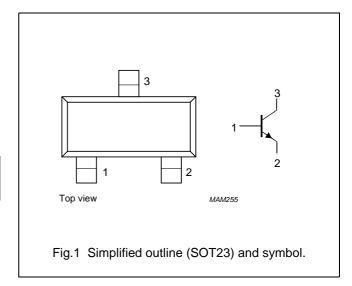
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBS3904	*04

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE		PACKAGE	
NUMBER	NAME	DESCRIPTION	VERSION
PMBS3904	_	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current capability		_	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

NPN general purpose transistor

PMBS3904

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

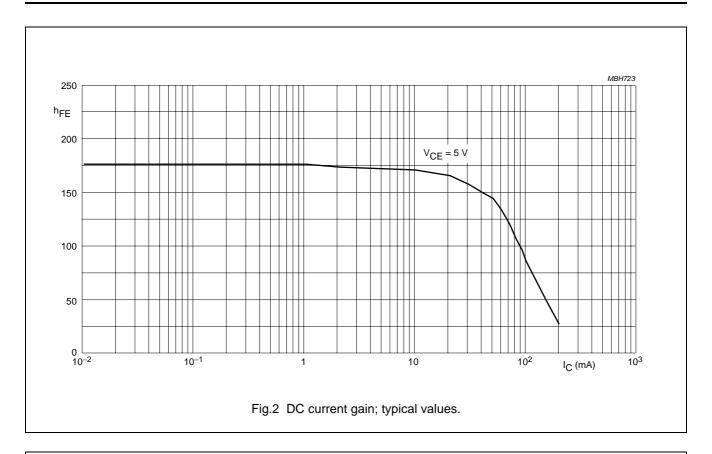
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	50	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	_	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; note 1; (see Fig.2)			
		$I_{C} = 0.1 \text{ mA}$	40	_	
		$I_C = 1 \text{ mA}$	70	_	
		I _C = 10 mA	100	300	
		I _C = 50 mA	60	_	
		I _C = 100 mA	30	_	
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 1 mA	_	200	mV
	voltage	I _C = 50 mA; I _B = 5 mA	_	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	650	850	mV
		I _C = 50 mA; I _B = 5 mA	_	950	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 5$ V; $f = 1$ MHz	_	4	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 0.5 \text{ V}$; $f = 1 \text{ MHz}$	_	12	pF
f _T	transition frequency	$I_C = 10 \text{ mA}$; $V_{CE} = 20 \text{ V}$; $f = 100 \text{ MHz}$	180	_	MHz
F	noise figure	I_C = 100 μA; V_{CE} = 5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	_	5	dB
Switching t	imes (between 10% and 90% lev	els); (see Fig.3)			
t _{on}	turn-on time	I _{Con} = 10 mA; I _{Bon} = 1 mA;	_	110	ns
t _d	delay time	$I_{Boff} = -1 \text{ mA}; V_{CC} = 3 \text{ V};$	_	50	ns
t _r	rise time	$V_{BB} = -1.9 \text{ V}$	_	60	ns
t _{off}	turn-off time	1	_	1200	ns
t _s	storage time	1	_	1000	ns
t _f	fall time	1	_	200	ns

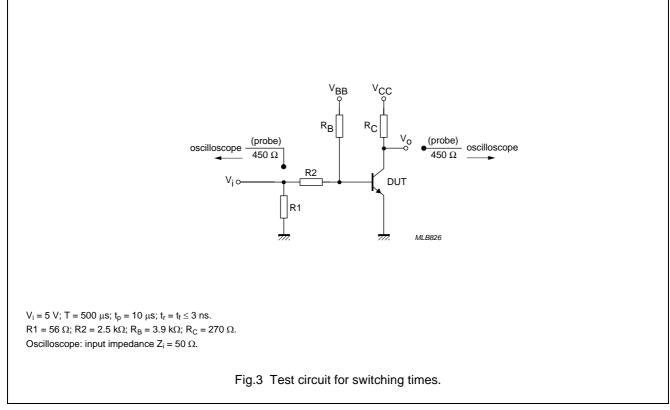
Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN general purpose transistor

PMBS3904





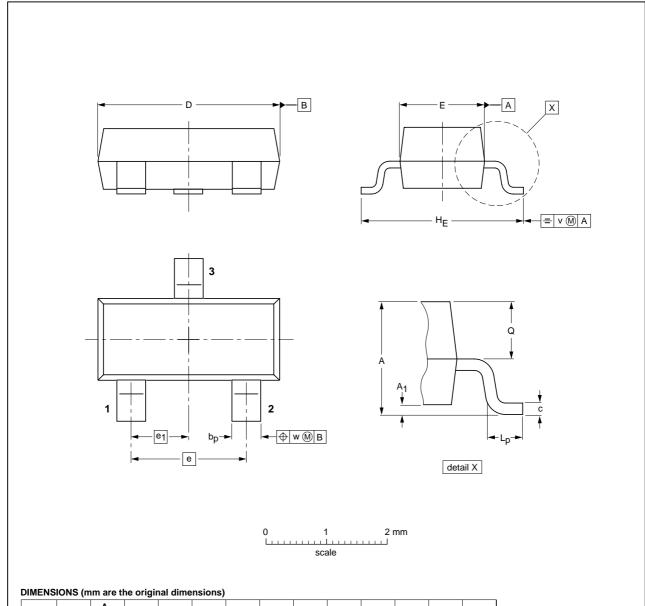
NPN general purpose transistor

PMBS3904

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



LINIT	Α	A ₁	h	D	F	

UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFERENCES EUROPEAN 1991					
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				-04-11-04 06-03-16	

2004 Feb 02 5

NPN general purpose transistor

PMBS3904

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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